

MBT2222ADW1T1G

General Purpose Transistor

NPN Silicon

Features

- Moisture Sensitivity Level: 1
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	V_{CEO}	40	Vdc
Collector–Base Voltage	V_{CBO}	75	Vdc
Emitter–Base Voltage	V_{EBO}	6.0	Vdc
Collector Current – Continuous	I_C	600	mAdc
Electrostatic Discharge	ESD	HBM Class 2 MM Class B	

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Package Dissipation (Note 1), $T_A = 25^\circ\text{C}$	P_D	150	mW
Thermal Resistance, Junction–to–Ambient	$R_{\theta JA}$	833	$^\circ\text{C/W}$
Junction and Storage Temperature	T_J, T_{stg}	–55 to +150	$^\circ\text{C}$

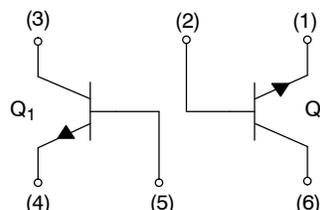
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Device mounted on FR4 glass epoxy printed circuit board using the minimum recommended footprint.



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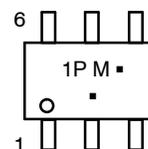
<http://onsemi.com>



1

SC-88/SC70-6/SOT-363
CASE 419B
STYLE 1

MARKING DIAGRAM



1P = Specific Device Code
M = Date Code
▪ = Pb-Free Package
(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping†
MBT2222ADW1T1G	SOT-363 (Pb-Free)	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Voltage (I _C = 10 mA _{dc} , I _B = 0)	V _{(BR)CEO}	40	-	V _{dc}
Collector-Base Breakdown Voltage (I _C = 10 μA _{dc} , I _E = 0)	V _{(BR)CBO}	75	-	V _{dc}
Emitter-Base Breakdown Voltage, (I _E = 10 μA _{dc} , I _C = 0)	V _{(BR)EBO}	6.0	-	V _{dc}
Collector Cutoff Current (V _{CE} = 60 V _{dc} , V _{EB(off)} = 3.0 V _{dc})	I _{CEX}	-	10	nA _{dc}
Collector Cutoff Current (V _{CB} = 60 V _{dc} , I _E = 0) (V _{CB} = 60 V _{dc} , I _E = 0, T _A = 125°C)	I _{CBO}	-	0.01 10	μA _{dc}
Emitter Cutoff Current (V _{EB} = 3.0 V _{dc} , I _C = 0)	I _{EBO}	-	100	nA _{dc}
Base Cutoff Current (V _{CE} = 60 V _{dc} , V _{EB(off)} = 3.0 V _{dc})	I _{BL}	-	20	nA _{dc}

ON CHARACTERISTICS

DC Current Gain (I _C = 0.1 mA _{dc} , V _{CE} = 10 V _{dc}) (I _C = 1.0 mA _{dc} , V _{CE} = 10 V _{dc}) (I _C = 10 mA _{dc} , V _{CE} = 10 V _{dc}) (I _C = 10 mA _{dc} , V _{CE} = 10 V _{dc} , T _A = -55°C) (I _C = 150 mA _{dc} , V _{CE} = 10 V _{dc}) (Note 2) (I _C = 150 mA _{dc} , V _{CE} = 1.0 V _{dc}) (Note 2) (I _C = 500 mA _{dc} , V _{CE} = 10 V _{dc}) (Note 2)	h _{FE}	35 50 75 35 100 50 40	- - - - 300 - -	-
Collector-Emitter Saturation Voltage (Note 2) (I _C = 150 mA _{dc} , I _B = 15 mA _{dc}) (I _C = 500 mA _{dc} , I _B = 50 mA _{dc})	V _{CE(sat)}	- -	0.3 1.0	V _{dc}
Base-Emitter Saturation Voltage (Note 2) (I _C = 150 mA _{dc} , I _B = 15 mA _{dc}) (I _C = 500 mA _{dc} , I _B = 50 mA _{dc})	V _{BE(sat)}	0.6 -	1.2 2.0	V _{dc}

SMALL-SIGNAL CHARACTERISTICS

Current-Gain - Bandwidth Product (Note 3) (I _C = 20 mA _{dc} , V _{CE} = 20 V _{dc} , f = 100 MHz)	f _T	300	-	MHz
Output Capacitance (V _{CB} = 10 V _{dc} , I _E = 0, f = 1.0 MHz)	C _{obo}	-	8.0	pF
Input Capacitance (V _{EB} = 0.5 V _{dc} , I _C = 0, f = 1.0 MHz)	C _{ibo}	-	25	pF
Input Impedance (I _C = 1.0 mA _{dc} , V _{CE} = 10 V _{dc} , f = 1.0 kHz) (I _C = 10 mA _{dc} , V _{CE} = 10 V _{dc} , f = 1.0 kHz)	h _{ie}	2.0 0.25	8.0 1.25	kΩ
Voltage Feedback Ratio (I _C = 1.0 mA _{dc} , V _{CE} = 10 V _{dc} , f = 1.0 kHz) (I _C = 10 mA _{dc} , V _{CE} = 10 V _{dc} , f = 1.0 kHz)	h _{re}	- -	8.0 4.0	X 10 ⁻⁴
Small-Signal Current Gain (I _C = 1.0 mA _{dc} , V _{CE} = 10 V _{dc} , f = 1.0 kHz) (I _C = 10 mA _{dc} , V _{CE} = 10 V _{dc} , f = 1.0 kHz)	h _{fe}	50 75	300 375	-
Output Admittance (I _C = 1.0 mA _{dc} , V _{CE} = 10 V _{dc} , f = 1.0 kHz) (I _C = 10 mA _{dc} , V _{CE} = 10 V _{dc} , f = 1.0 kHz)	h _{oe}	5.0 25	35 200	μmhos
Collector Base Time Constant (I _E = 20 mA _{dc} , V _{CB} = 20 V _{dc} , f = 31.8 MHz)	r _b , C _c	-	150	ps
Noise Figure (I _C = 100 μA _{dc} , V _{CE} = 10 V _{dc} , R _S = 1.0 kΩ, f = 1.0 kHz)	NF	-	4.0	dB

SWITCHING CHARACTERISTICS

Delay Time	(V _{CC} = 30 V _{dc} , V _{BE(off)} = -0.5 V _{dc} , I _C = 150 mA _{dc} , I _{B1} = 15 mA _{dc})	t _d	-	10	ns
Rise Time		t _r	-	25	
Storage Time	(V _{CC} = 30 V _{dc} , I _C = 150 mA _{dc} , I _{B1} = I _{B2} = 15 mA _{dc})	t _s	-	225	ns
Fall Time		t _f	-	60	

2. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

3. f_T is defined as the frequency at which |h_{fe}| extrapolates to unity.

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SWITCHING TIME EQUIVALENT TEST CIRCUITS

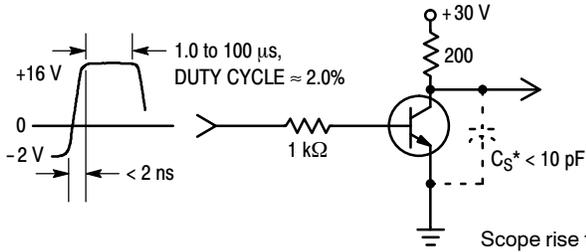


Figure 1. Turn-On Time

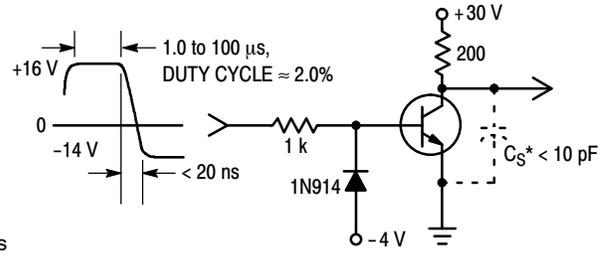


Figure 2. Turn-Off Time

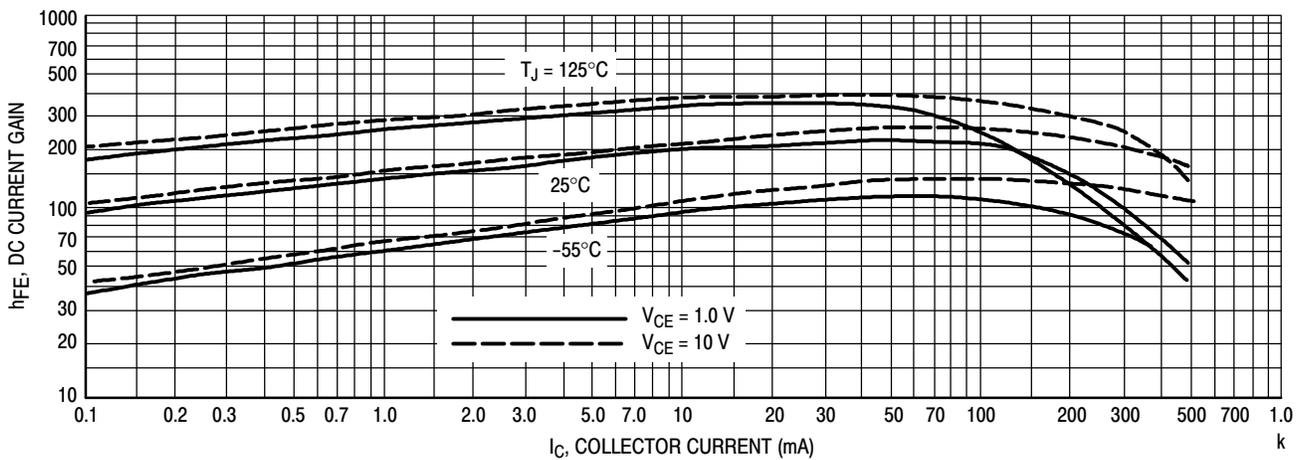


Figure 3. DC Current Gain

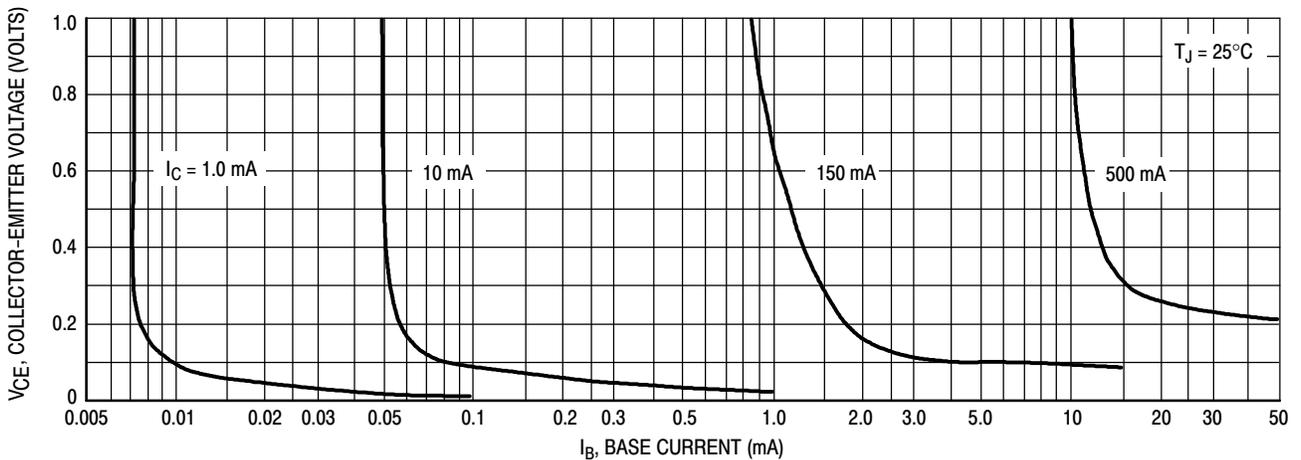


Figure 4. Collector Saturation Region

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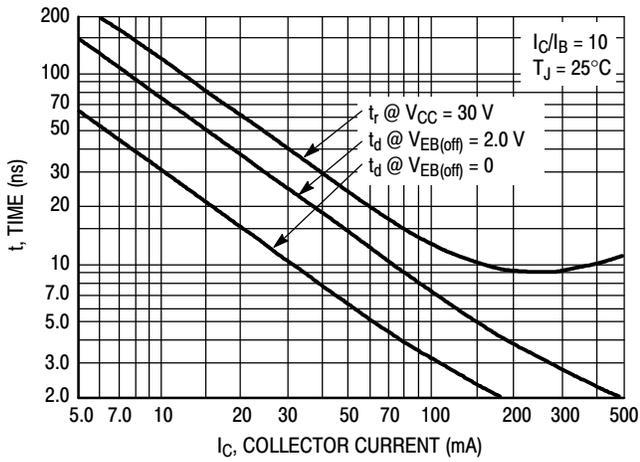


Figure 5. Turn-On Time

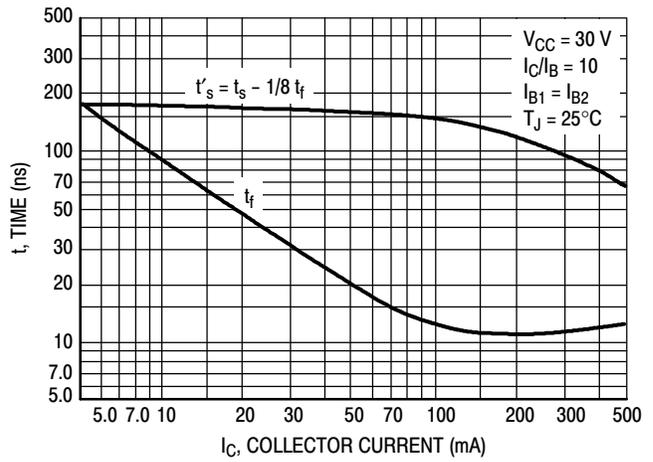


Figure 6. Turn-Off Time

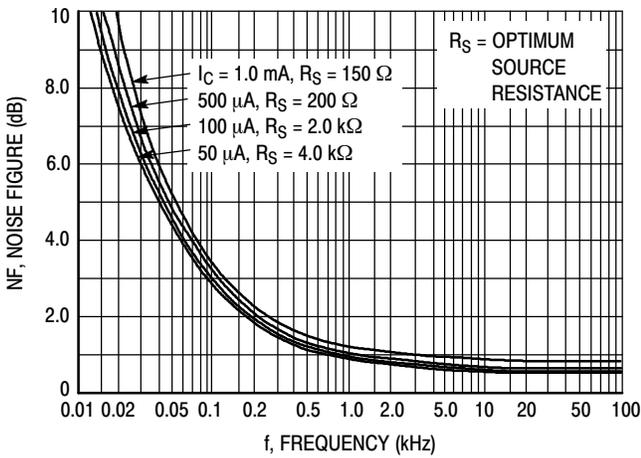


Figure 7. Frequency Effects

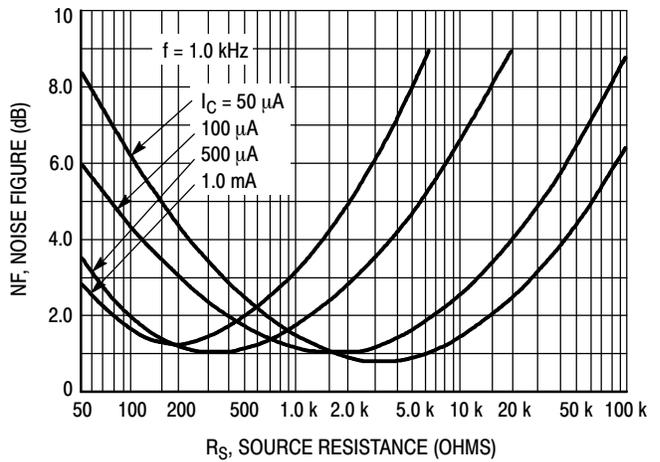


Figure 8. Source Resistance Effects

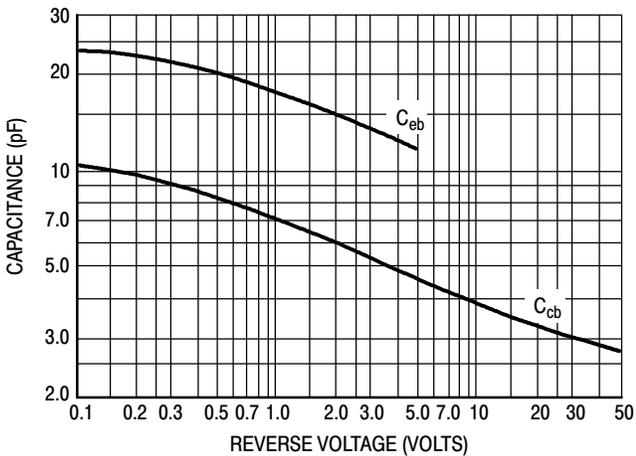


Figure 9. Capacitances

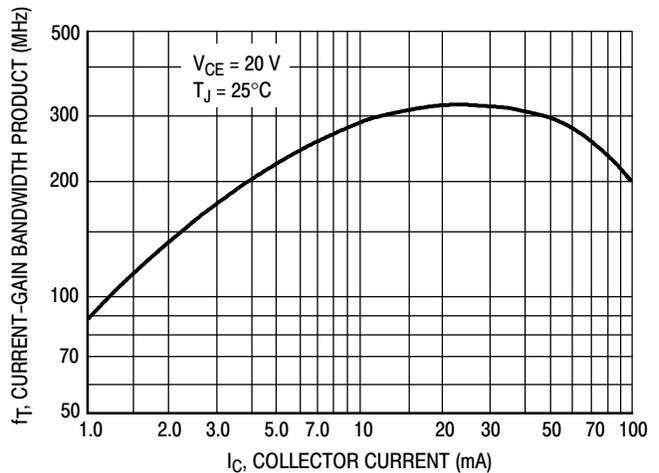


Figure 10. Current-Gain Bandwidth Product

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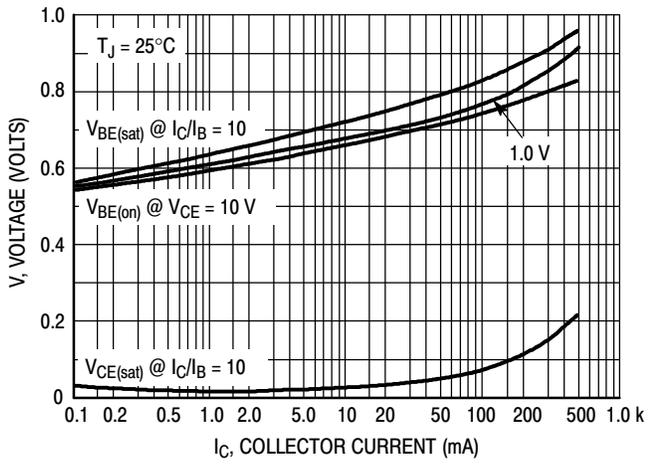


Figure 11. "On" Voltages

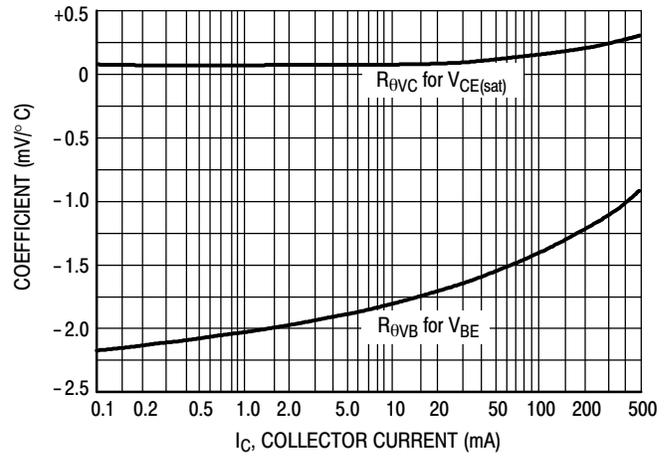
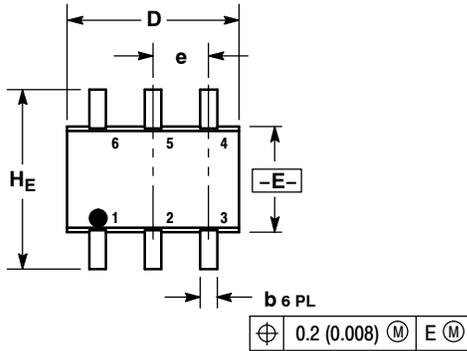


Figure 12. Temperature Coefficients

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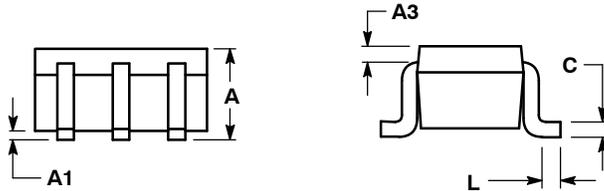
PACKAGE DIMENSIONS

SC-88/SC70-6/SOT-363
CASE 419B-02
ISSUE W



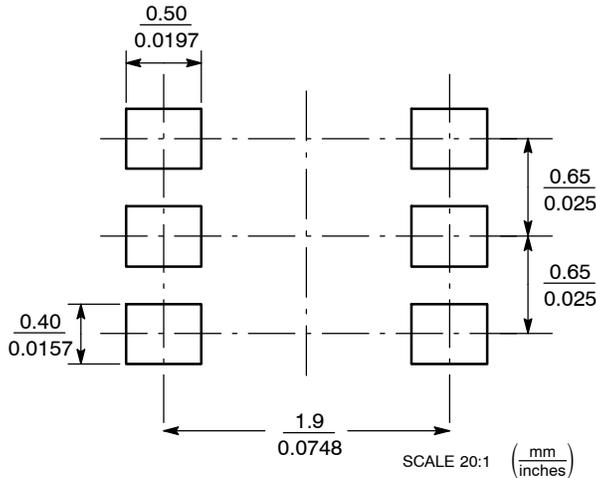
- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 3. 419B-01 OBSOLETE, NEW STANDARD 419B-02.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.80	0.95	1.10	0.031	0.037	0.043
A1	0.00	0.05	0.10	0.000	0.002	0.004
A3	0.20 REF			0.008 REF		
b	0.10	0.21	0.30	0.004	0.008	0.012
C	0.10	0.14	0.25	0.004	0.005	0.010
D	1.80	2.00	2.20	0.070	0.078	0.086
E	1.15	1.25	1.35	0.045	0.049	0.053
e	0.65 BSC			0.026 BSC		
L	0.10	0.20	0.30	0.004	0.008	0.012
HE	2.00	2.10	2.20	0.078	0.082	0.086



- STYLE 1:
PIN 1. EMITTER 2
2. BASE 2
3. COLLECTOR 1
4. EMITTER 1
5. BASE 1
6. COLLECTOR 2

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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